FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. SEPP21.001C1	APPLICATION NO. 10/678,766
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	APPLICANT TOIS et al.	
(USE SEVERAL SHEETS IF NECESSARY)	FILING DATE October 2, 2003	GROUP 1765

U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
M)	1.	5,480,818	01/02/96	Matsumoto et al.	437	40	02/09/93
M>	2.	6,006,763	12/28/99	Mori et al.			

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
M>	3.	JP 3286531 A2	12.17.91	Japan Abstract				
M)	4.	JP 60065712 A2	04.15.85	Japan Abstract				

EXAMINER INITIAL		OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
M)	5	Klaus, J. W. et al., "Atomic Layer Deposition of SiO_2 Using Catalyzed and Uncatalyzed Self-Limiting Surface Reactions," Surface Review and Letters, Vol. 6, Nos. 3 & 4, pp. 435-448 (1999).
	6	Niinistö, L. et al., "Synthesis of oxide thin films and overlayers by atomic layer epitaxy for advanced applications," Materials Science and Engineering, B41, pp. 23-29 (1996).
	7	Wise, M. L. et al., "Diethyldiethoxysilane as a New Precursor for SiO_2 Growth on Silicon," Mat. Res. Soc. Symp. Proc., Vol. 334, pp. 37-43 (1994).
	8	Yamaguchi, Kei-ichi et al., "Atomic-layer chemical-vapor-deposition of silicon dioxide films with an extremely low hydrogen content.", Appl. Surf. Science, 130-132; pp. 202-207 (1998)
	9	George, S.M., et al., "Surface Chemistry for Atomic Layer Growth," J. Phys. Chem., 100:13121-13131 (1996)
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	11	Jeon, H., "A Study on the Characteristics of TiN Thin Film Deposited by Atomic Layer Chemical Vapor Deposition Method," *AVS 46th International Symposium*, Seattle, WA, abstract TF-MoP17 (1999)
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	13	Klaus, J.W., et al., "Atomically controlled growth of tungsten and tungsten nitride using sequential surface reactions," *Appl. Surf. Science* 162-163; 479-471 (2000)
	14	Klaus, J.W., et al., "Atomic layer deposition of tungsten nitride films using sequential surface reactions," *Journal of the Electrochemical Soc.*, 147 (3):1175-1181 (2000)
	15	Klaus, J.W. et al., "Atomic layer deposition of tungsten using sequential surface chemistry with a sacrificial stripping reaction," *Thin Solid Films*, 360:145-153 (2000)n
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EXAMINER	DATE CONSIDERED 9/25/2004

*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.